

[CLEANING METHOD USED IN INTER-CONNECT PROCESS]

Abstract

A cleaning method used in the fabrication of metallic interconnects is provided. A substrate having a conductive layer and a dielectric layer on the conductive layer is provided. An opening is formed in the dielectric layer. The opening exposes a portion of the conductive layer. The opening is cleaned using a mixture containing sulfuric acid and hydrogen peroxide. In this invention, the mixture containing sulfuric acid and hydrogen peroxide provides an effective means of removing the residues within the opening so that the electrical conductivity of a subsequently formed contact is improved.